

photoresist layer is between approximately 0.1 to 0.2 μ m thick and covers a substantial amount of an active area comprising a source region and a drain region of the semiconductor device; and

(b) providing the halo implant to the semiconductor device, wherein the thin photoresist layer is used as a mask.

Please cancel claims 2, 3 and 6.

8. (Twice Amended) A system for providing a halo implant to a semiconductor device comprising:
means for providing a thin photoresist layer to the semiconductor device, wherein the thin photoresist layer is between approximately 0.1 to 0.2 μ m thick and covers a substantial amount of an active area comprising a source region and a drain region of the semiconductor device; and
means for providing the halo implant to the semiconductor device, wherein the thin photoresist layer is used as a mask.

Please cancel claims 9 and 13.

IN THE ABSTRACT

A method and system for providing a halo implant to a semiconductor device is disclosed. The method and system comprises providing a thin photoresist layer between approximately 0.1 to 0.2 μ m thick to the semiconductor device, wherein the thin photoresist layer covers a substantial amount of an active area comprising a source region and a drain region of the semiconductor device. The method and system further includes providing the halo implant to the to the